## LASER DIODE <br> NDL5071

## 1550 nm OPTICAL FIBER COMMUNICATION InGaAsP DOUBLE HETEROSTRUCTURE PULSED LASER DIODE

## DESCRIPTION

NDL5071 is a 1550 nm pulsed laser diode especially designed for optical measurement equipment (OTDR). The DC-PBH (Double Channel Planar Buried Heterostructure) can achieve stable fundamental oscillation in wide temperature range. It incorporates ball lens and achieves collimated beam for easy optical coupling.

## PACKAGE DIMENSIONS



## FEATURES

- High output power. $P_{P}=50 \mathrm{~mW}$ MIN. @| $\mathrm{F}_{\mathrm{FP}}=400 \mathrm{~mA}$ *
- Long wavelength. $\lambda_{P}=1550 \mathrm{~nm}$
- Low threshold current. $I_{t h}=40 \mathrm{~mA}$ TYP.
- Internal ball lens.
- Wide operating temperature range.

ABSOLUTE MAXIMUM RATINGS ( $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$ )

| Reverse Voltage | $\mathrm{V}_{\mathrm{R}}$ | 2.0 | V |
| :--- | :--- | :---: | :---: |
| Pulse Forward Current * | $\mathrm{I}_{\mathrm{FP}}$ | 600 | mA |
| Operating Case Temperature | $\mathrm{T}_{\mathrm{c}}$ | -40 to +70 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature | $\mathrm{T}_{\mathrm{stg}}$ | -55 to +125 | ${ }^{\circ} \mathrm{C}$ |

* Pulse Condition: PW (Pulse Width) $=1 \mu \mathrm{~s}$, Duty $=1 \%$

ELECTRO-OPTICAL CHARACTERISTICS (T $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$ )

| CHARACTERISTIC | SYMBOL | MIN. | TYP. | MAX. | UNIT | TEST CONDITIONS |
| :--- | :---: | :---: | :---: | :---: | :---: | :---: |
| Forward Voltage | $\mathrm{V}_{\mathrm{F}}$ |  | 1.0 | 1.5 | V | $\mathrm{I}_{\mathrm{F}}=30 \mathrm{~mA}$ |
| Threshold Current | $\mathrm{I}_{\mathrm{th}}$ |  | 40 | 60 | mA |  |
| Optical Output Power | $\mathrm{P}_{\mathrm{P}}$ | 50 |  |  | mW | $\mathrm{I}_{\mathrm{FP}}=400 \mathrm{~mA}, \mathrm{PW}=1 \mu \mathrm{~s}$, Duty $=1 \%$ |
| Peak Emission Wavelength | $\lambda_{\mathrm{P}}$ | 1520 | 1550 | 1580 | nm | $\mathrm{I}_{\mathrm{FP}}=400 \mathrm{~mA}, \mathrm{PW}=1 \mu \mathrm{~s}$, Duty $=1 \%$ |
| Half Power Spectral Width | $\Delta \lambda$ |  |  | 20 | nm | $I_{\mathrm{FP}}=400 \mathrm{~mA}, \mathrm{PW}=1 \mu \mathrm{~s}, \mathrm{Duty}=1 \%$ |
| Rise Time | $\mathrm{t}_{\mathrm{r}}$ |  | 0.5 | 1.0 | ns | $10-90 \%$ |
| Fall Time | $\mathrm{t}_{\mathrm{f}}$ |  | 0.7 | 1.0 | ns | $90-10 \%$ |

TYPICAL CHARACTERISTICS ( $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$ )

$X-Y$ Beam Profile


X-Y Beam Profila


PULSED LD FAMILY

| Package Features <br> Package |  | 1300 nm |  | 1550 nm |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | ＠1FP $=250 \mathrm{~mA}$ | $@ ⿴ 囗 ⿱ 一 一 ⿸ 丆 口_{\text {FP }}=400 \mathrm{~mA}$ | $@ l_{F P}=250 \mathrm{~mA}$ | ＠1FP $=400 \mathrm{~mA}$ |  |
| Can with Ball lens |  | NDL5060 | NDL5061 | NDL5070 | NDL5071 |  |
| 14－pin DIP Module with Multi－Mode fiber（MMF） |  | NDL5062P |  | NDL5072P |  |  |
| MAIN CHARACTERISTICS |  |  |  |  |  | UNIT |
| Optical Output | $P_{p} \mathrm{MIN}$ ． | 50 | 90 | 30 | 50 | mW |
| Fiber Output | $P_{f}$ MIN． | 20 |  | 10 |  | mW |
| Peak Wavelength | $\lambda_{p}$ | $1310 \pm 20$ |  | $1550 \pm 30$ |  | nm |
| ＊Pulse Current | ＠1FP | 250 | 400 | 250 | 400 | mA |

＊Pulse Width $=1 \mu$ ，Duty $=1 \%$


VV/ INvisisele Laste Rabiation AVOIDDIRECT EXPOSUPE TO BEAM OUTPUT POWER _mw MAX WAVELENGTH MI
CLASS III LASER PRODUCT

## SEMICONDUCTOR LASER



AVOID EXPOSURE-Invisible Laser Radiation is emitted from this aperture

NEC Corporation
NEC Euilding, 33-1, Shiba Gochome, Minato-ku. Tokyo 108, Japan

Type number:
Manufactured: Serial number
This product conforms to DHHS regulations as applicable
to standards 21 CFR Chapter 1.
Subchapter J.

